
2SC2620

Silicon NPN Epitaxial Planar

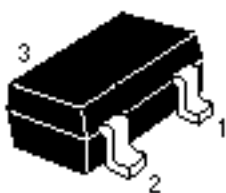
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Application

VHF amplifier, Local oscillator

Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector

2SC2620

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	4	V
Collector current	I_C	20	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

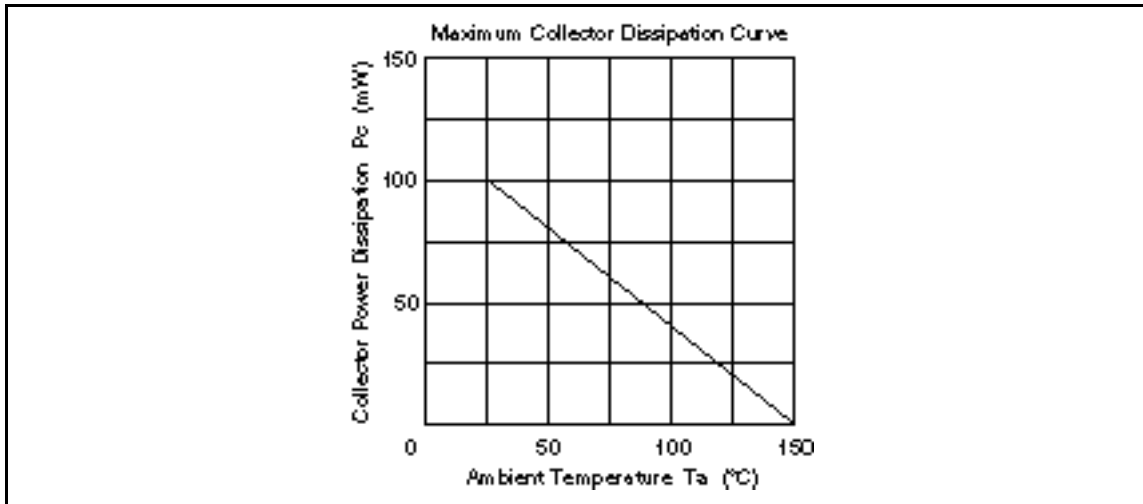
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	—	—	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 10 \text{ V}, I_C = 0$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB} = 2 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	60	—	200		$V_{CE} = 6 \text{ V}, I_C = 1 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.17	—	V	$I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$
Base to emitter voltage	V_{BE}	—	0.72	—	V	$V_{CE} = 6 \text{ mA}, I_C = 1 \text{ mA}$
Gain bandwidth product	f_T	—	940	—	MHz	$V_{CE} = 6 \text{ V}, I_C = 5 \text{ mA}$
Collector output capacitance	C_{ob}	—	0.9	—	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Note: 1. The 2SC2620 is grouped by h_{FE} as follows.

Grade	B	C
Mark	QB	QC
h_{FE}	60 to 120	100 to 200

See characteristic curves of 2SC535.



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